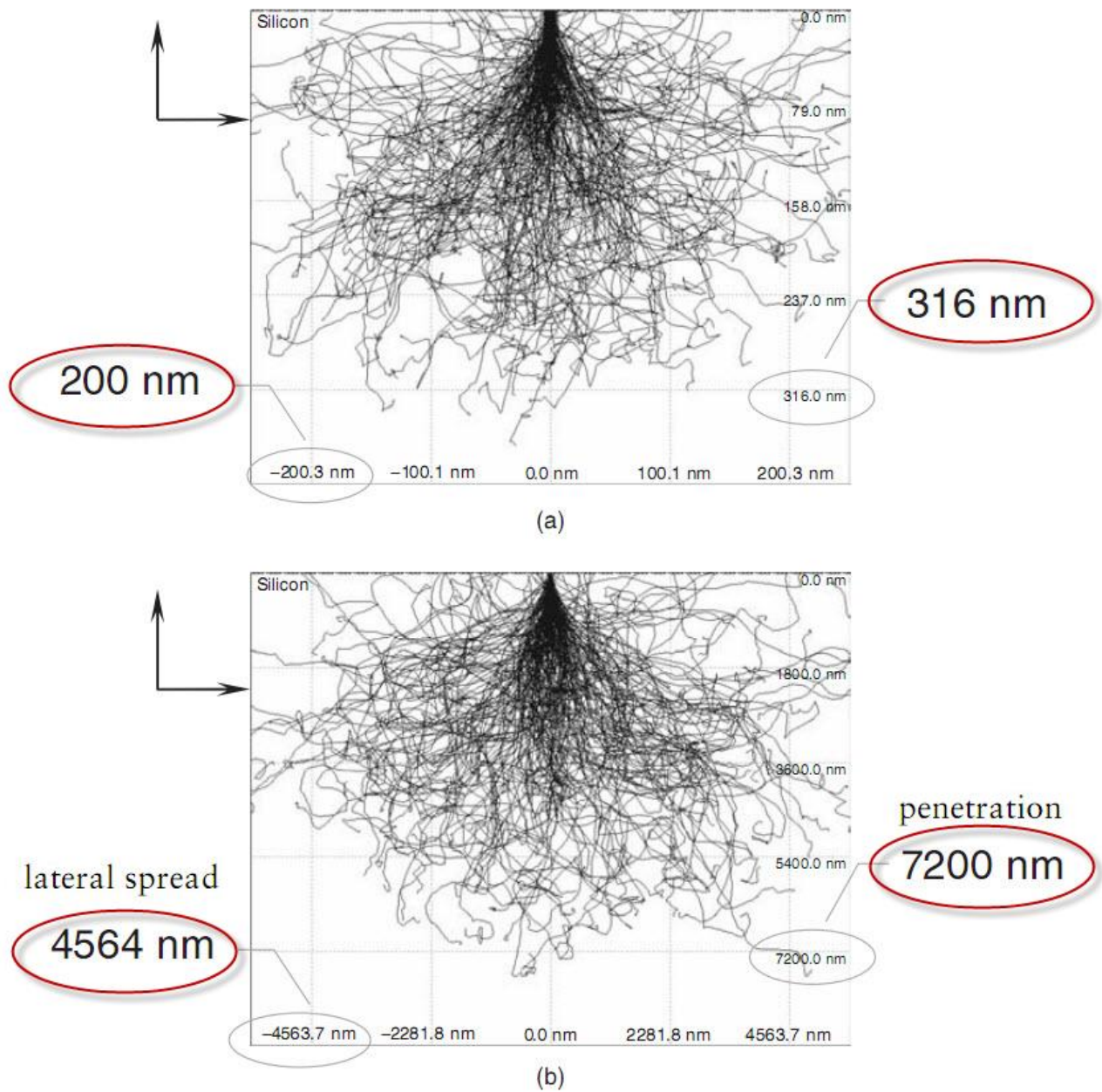




The interaction volumes for low vs high primary electron energy E_0 in a silicon substrate ($Z = 14$). (a) $E_0 = 5$ keV; (b) $E_0 = 30$ keV. The lateral spread and penetration depth are much increased in the case of (b).

Monte Carlo simulation